ALPHA & OMEGA SEMICONDUCTOR

AOU412
N-Channel Enhancement Mode Field Effect Transistor

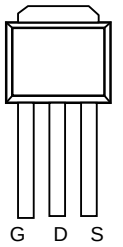
General Description

The AOU412 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate chargeand low gate resistance. This device is ideally suited for use as a high side switch in CPU core power conversion. *Standard Product AOU412 is Pb-free (meets ROHS & Sony 259 specifications). AOU412L is a Green Product ordering option. AOU412 and AOU412L are electrically identical.*

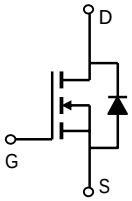
Features

V_{DS} (V) = 30V
I_D = 85A (V_{GS} = 10V)
$R_{DS(ON)}$ < 7.5mΩ (V_{GS} = 10V)
$R_{DS(ON)}$ < 11mΩ (V_{GS} = 4.5V)

TO-251



Top View
Drain
Connected to
Tab



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [B,G]	T_C=25°C [G]	I_D	85	A
	T_C=100°C [B]		65	
Pulsed Drain Current		I_{DM}	200	
Avalanche Current [C]		I_{AR}	30	A
Repetitive avalanche energy L=0.1mH [C]		E_{AR}	120	mJ
Power Dissipation [B]	T_C=25°C	P_D	100	W
	T_C=100°C		50	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	Steady-State	$R_{\theta JA}$	105	125	°C/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	1	1.5	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=24V, V_{GS}=0V		0.005	1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±20V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA	1.5	2.15	2.5	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V	85			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A		5.7	7.5	mΩ
		T_J=125°C		8.4	10	
		V_{GS}=4.5V, I_D=20A		8.7	11	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		60		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.72	1	V
I_S	Maximum Body-Diode Continuous Current				85	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		1320	1600	pF
C_{oss}	Output Capacitance			533		pF
C_{rss}	Reverse Transfer Capacitance			154		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		0.95	1.2	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=4.5V, V_{DS}=15V, I_D=20A		26	32	nC
Q_g(4.5V)	Total Gate Charge			13.3	16.2	nC
Q_{gs}	Gate Source Charge			3.2		nC
Q_{gd}	Gate Drain Charge			6.6		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=0.75Ω, R_{GEN}=3Ω		7.2	10	ns
t_r	Turn-On Rise Time			12.5	18	ns
$t_{D(off)}$	Turn-Off DelayTime			22	33	ns
t_f	Turn-Off Fall Time			6	9	ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, dI/dt=100A/µs		29.7	36	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, dI/dt=100A/µs		29	36	nC

A: The value of $R_{\theta JA}$ is measured with the device in a still air environment with T_A =25°C.

B. The power dissipation P_D is based on $T_{J(MAX)}$=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=175°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=175°C.

G. The maximum current rating is limited by bond-wires.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

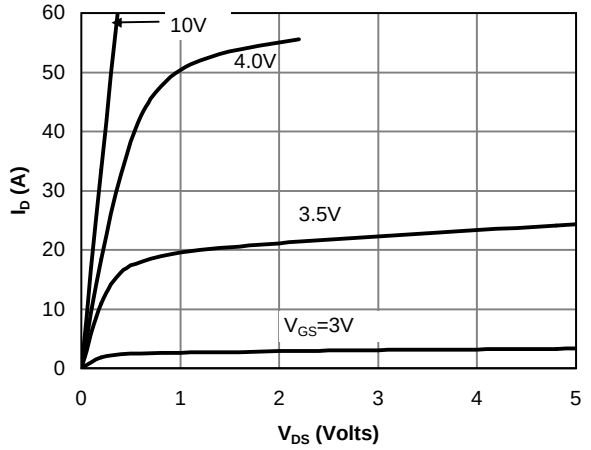

Fig 1: On-Region Characteristics

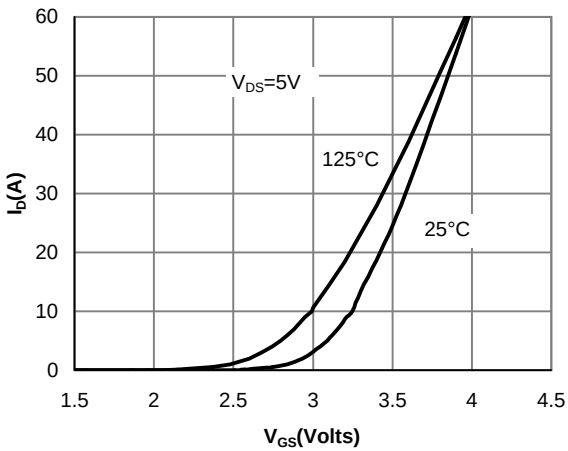

Figure 2: Transfer Characteristics

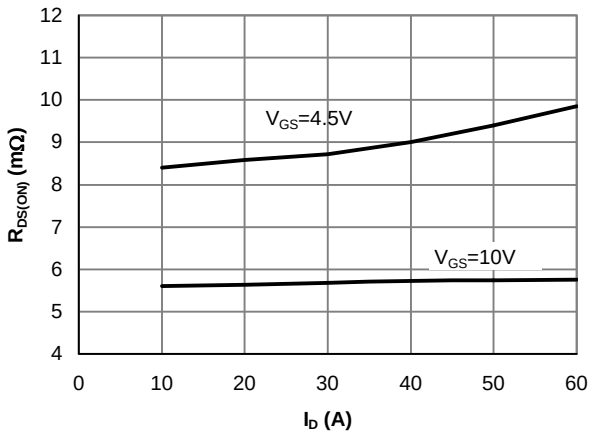

Figure 3: On-Resistance vs. Drain Current and Gate Voltage

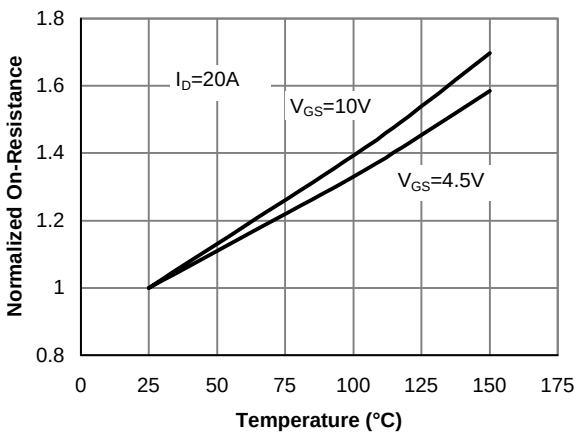

Figure 4: On-Resistance vs. Junction Temperature

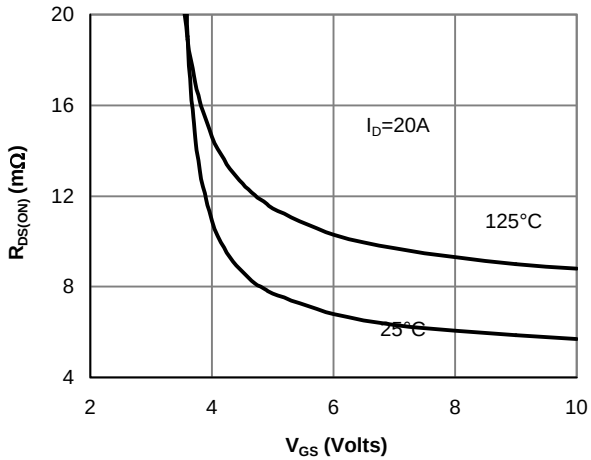

Figure 5: On-Resistance vs. Gate-Source Voltage

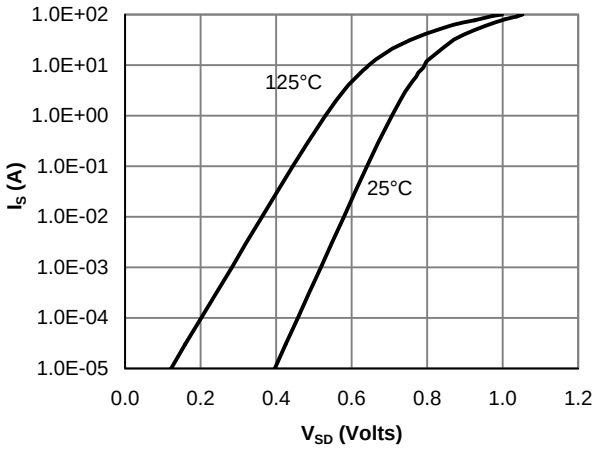

Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

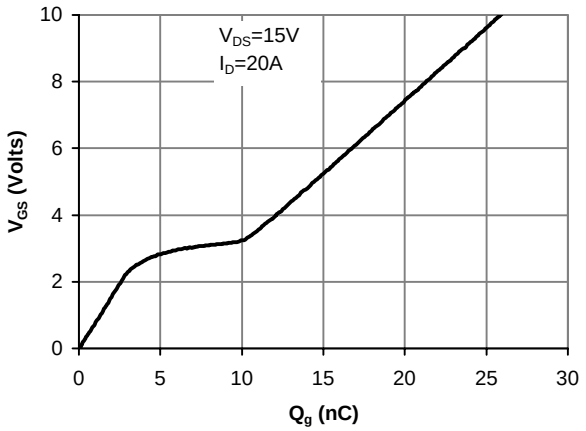

Figure 7: Gate-Charge Characteristics

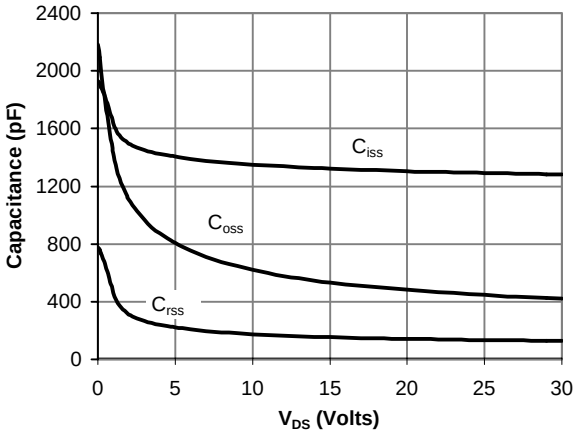

Figure 8: Capacitance Characteristics

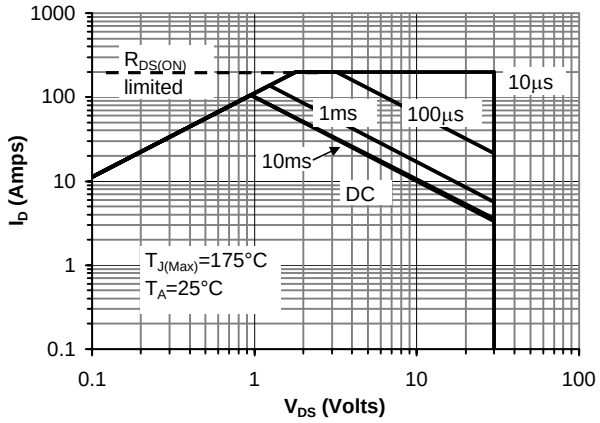

Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

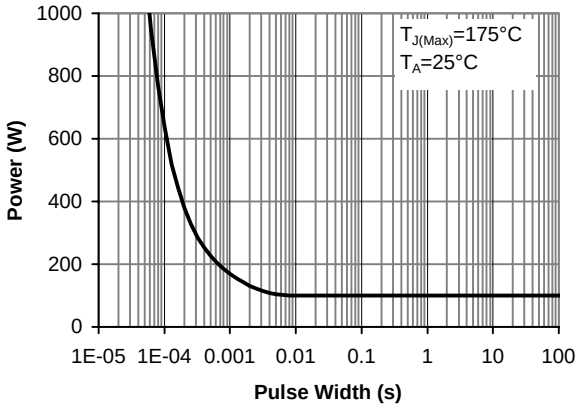

Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

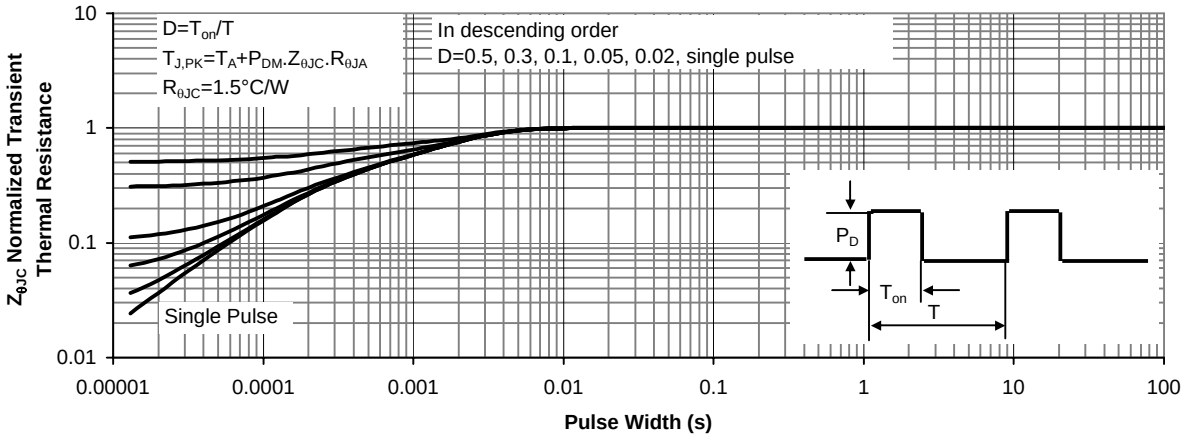

Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

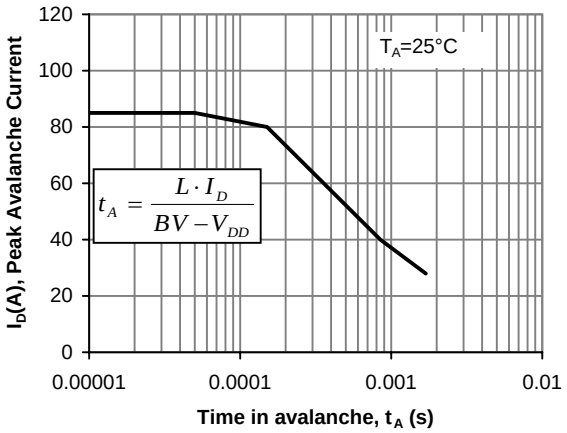

Figure 12: Single Pulse Avalanche capability

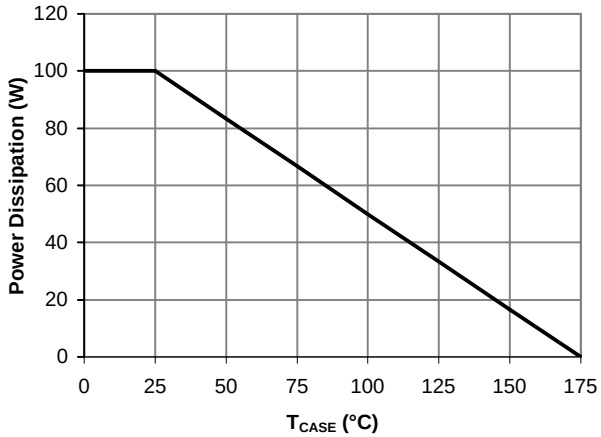

Figure 13: Power De-rating (Note B)

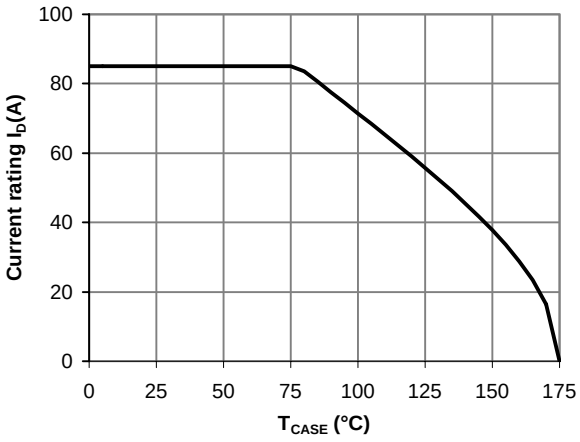

Figure 14: Current De-rating (Note B)